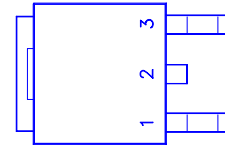
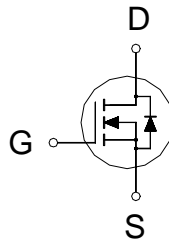


**PRODUCT SUMMARY**

$V_{(BR)DSS}$	$R_{DS(ON)}$	$I_D$
25	5m	75A



1. GATE
2. DRAIN
3. SOURCE

**ABSOLUTE MAXIMUM RATINGS ( $T_C = 25\text{ }^\circ\text{C}$  Unless Otherwise Noted)**

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Gate-Source Voltage		$V_{GS} \pm$	20	V
Continuous Drain Current	$T_C = 25\text{ }^\circ\text{C}$	$I_D$	75	A
	$T_C = 100\text{ }^\circ\text{C}$		50	
Pulsed Drain Current <sup>1</sup>		$I_{DM}$	170	
Avalanche Current		$I_{AR}$	60	
Avalanche Energy	$L = 0.1\text{mH}$	$E_{AS}$	140	mJ
Repetitive Avalanche Energy <sup>2</sup>	$L = 0.05\text{mH}$	$E_{AR}$	5.6	
Power Dissipation	$T_C = 25\text{ }^\circ\text{C}$	$P_D$	60	W
	$T_C = 100\text{ }^\circ\text{C}$		32.75	
Operating Junction & Storage Temperature Range		$T_j, T_{stg}$	-55 to 150	$^\circ\text{C}$
Lead Temperature ( <sup>1</sup> / <sub>16</sub> " from case for 10 sec.)		$T_L$ 275		

**THERMAL RESISTANCE RATINGS**

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Case	$R_{\theta JC}$		2.3	$^\circ\text{C} / \text{W}$
Junction-to-Ambient	$R_{\theta JA}$		62.5	
Case-to-Heatsink	$R_{\theta CS}$	0.6		

<sup>1</sup>Pulse width limited by maximum junction temperature.

<sup>2</sup>Duty cycle  $\leq 1\%$

**ELECTRICAL CHARACTERISTICS ( $T_C = 25\text{ }^\circ\text{C}$ , Unless Otherwise Noted)**

PARAMETER SY	MBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	YP	MAX	
<b>STATIC</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$	25			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	1	1.5	3	
Gate-Body Leakage	$I_{GSS} V$	$V_{DS} = 0\text{V}, V_{GS} = \pm 20\text{V}$			$\pm 250$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 20\text{V}, V_{GS} = 0\text{V}$			25	$\mu\text{A}$
		$V_{DS} = 20\text{V}, V_{GS} = 0\text{V}, T_J = 125\text{ }^\circ\text{C}$			250	

On-State Drain Current <sup>1</sup>	$I_{D(ON)}$	$V_{DS} = 10V, V_{GS} = 10V$	70			A
Drain-Source On-State Resistance <sup>1</sup>	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 30A$		5	7	m
		$V_{GS} = 7V, I_D = 24A$		6	8	
Forward Transconductance <sup>1</sup>	$g_{fs}$	$V_{DS} = 15V, I_D = 30A$		16		S
<b>DYNAMIC</b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0V, V_{DS} = 15V, f = 1MHz$		5000		pF
Output Capacitance	$C_{oss}$			1800		
Reverse Transfer Capacitance	$C_{rss}$			800		
Total Gate Charge <sup>2</sup>	$Q_g$	$V_{DS} = 0.5V_{(BR)DSS}, V_{GS} = 10V, I_D = 35A$		140		nC
Gate-Source Charge <sup>2</sup>	$Q_{gs}$			40		
Gate-Drain Charge <sup>2</sup>	$Q_{gd}$			75		
Turn-On Delay Time <sup>2</sup>	$t_{d(on)}$	$V_{DS} = 15V, R_L = 1 \Omega, I_D \cong 30A, V_{GS} = 10V, R_{GS} = 2.5 \Omega$		7		nS
Rise Time <sup>2</sup>	$t_r$			7		
Turn-Off Delay Time <sup>2</sup>	$t_{d(off)}$			24		
Fall Time <sup>2</sup>	$t_f$			6		
<b>SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (<math>T_C = 25^\circ C</math>)</b>						
Continuous Current	$I_S$				75	A
Pulsed Current <sup>3</sup> I	$I_{SM}$				170	
Forward Voltage <sup>1</sup> V	$V_{SD}$	$I_F = I_S, V_{GS} = 0V$			1.3	V
Reverse Recovery Time	$t_{rr}$	$I_F = I_S, di_F/dt = 100A / \mu S$		37		nS
Peak Reverse Recovery Current	$I_{RM(REC)}$			200		A
Reverse Recovery Charge	$Q_{rr}$				0.043	

<sup>1</sup>Pulse test : Pulse Width  $\leq 300 \mu sec$ , Duty Cycle  $\leq 2\%$ .

<sup>2</sup>Independent of operating temperature.

<sup>3</sup>Pulse width limited by maximum junction temperature.

**REMARK: THE PRODUCT MARKED WITH "P75N02LDG", DATE CODE or LOT #**

**Orders for parts with Lead-Free plating can be placed using the PXXXXXXG parts name.**

**TO-252 (DPAK) MECHANICAL DATA**

Dimension	mm			Dimension	mm		
	Min. T	yp.	Max.		Min. T	yp.	Max.
A	9.35	10.4		H	0.89		2.03
B	2.2	2.4		I	6.35		6.80
C	0.45		0.6 J 5.2				5.5
D	0.89	1.5		K	0.6		1
E	0.45	0.69		L 0.5			0.9
F	0.03	0.23		M	3.96	4.57	5.18
G	5.2	6.2		N			

